

an upper electrode formed on the capacitive insulating film;  
a contact layer formed on the upper electrode;  
an insulating film formed to cover the lower electrode, the capacitive insulating film, the upper electrode and the contact layer;  
a contact hole passing through the insulating film and the contact layer to reach the upper electrode; and  
*a<sup>1</sup> Cont*  
a metal interconnect, which is defined on a part of the insulating film, provided at least in the contact hole and connected to the upper electrode,  
wherein the ferroelectric film includes SrBi<sub>2</sub>Ta<sub>2</sub>O<sub>9</sub>, and  
wherein the contact layer is a single layer film or a multilayer structure, the single-layer film being made of a metal oxide or a metal nitride, the multilayer structure being made up of metal oxide and metal nitride films.

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Please add the following new claims 6-9:

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--6. (New) A semiconductor device comprising:

*a<sup>2</sup>*  
a lower electrode formed on a substrate;  
a capacitive insulating film formed out of a ferroelectric film on the lower electrode;  
an upper electrode formed on the capacitive insulating film;  
a contact layer formed on the upper electrode;  
an insulating film formed to cover the lower electrode, the capacitive insulating film, the upper electrode and the contact layer;  
a contact hole passing through the insulating film and the contact layer to reach the upper

electrode; and

a metal interconnect, which is defined on a part of the insulating film, provided at least in the contact hole and connected to the upper electrode,

112 /st wherein the ferroelectric film includes [a crystal composed of Sr, Bi, Ta and O] and wherein the contact layer is a single-layer film or a multilayer structure, the single-layer film being made of a metal oxide or a metal nitride, the multilayer structure being made up of metal oxide and metal nitride films.

7. (New) The device of Claim 6,

wherein the upper electrode contains Pt or Ir, and

wherein the metal oxide film is made of an oxide of Ti or an oxide of Ta, while the metal nitride film is made of a nitride of Ti or a nitride of Ta.

8. (New) A semiconductor device comprising:

a lower electrode formed on a substrate;

a capacitive insulating film formed out of a ferroelectric film on the lower electrode;

an upper electrode formed on the capacitive insulating film;

a contact layer formed on the upper electrode;

an insulating film formed to cover the lower electrode, the capacitive insulating film, the upper electrode and the contact layer;

a contact hole passing through the insulating film and the contact layer to reach the upper electrode; and

a metal interconnect, which is defined on a part of the insulating film, provided at least in